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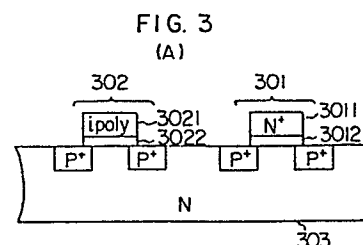
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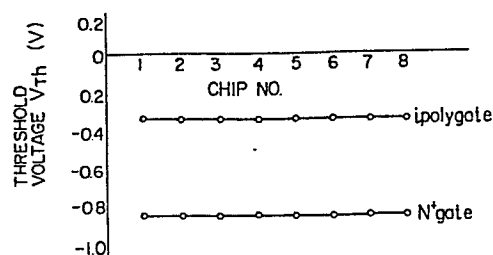
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54 Reference voltage generating device.

57 A reference voltage generating device comprises a first MOS transistor whose gate electrode (3011) is formed of an N-type semiconductor of a semiconductive material and a second MOS transistor whose gate electrode (3021) is formed of an intrinsic semiconductor (3021) of the same semiconductive material. In the device, the voltage corresponding to the difference between the Fermi energy levels of the semiconductors (3011, 3021) is derived utilizing the threshold voltage difference ($V_{thi} - V_{thn+}$) between the first and second MOS transistors.



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EUROPEAN SEARCH REPORT

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DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl. 7)
X	US-A-4 206 946 (R.C.A.) * Column 2, lines 9-43; figure 1 *	1-3,12	G 05 F 3/20
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Y	ELECTRONIC ENGINEERING, vol. 52, no. 638, May 1980, pages 65-85, London, GB; M.A. REHMAN: "Integrated circuit voltage reference" * Figure 13 *	4	
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D,A	DE-A-2 951 835 (CENTRE ELECTRONIQUE HORLOGER) ---		G 05 F
D,A	IEEE JOURNAL OF SOLID-STATE CIRCUITS, vol. SC-15, no. 3, June 1980, pages 264-269, IEEE, New York, US; H.J. OGUEY et al.: "MOS voltage reference based on polysilicon gate work function difference" -----		
The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 06-08-1984	Examiner HOUILLOIN J.C.P.L.
CATEGORY OF CITED DOCUMENTS X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document			